

FDT1600N10ALZ

N 沟道 PowerTrench® MOSFET

100 V, 5.6 A, 160 mΩ

特性

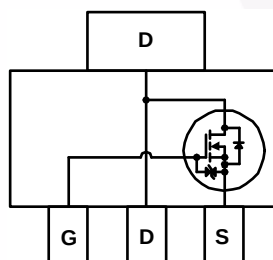
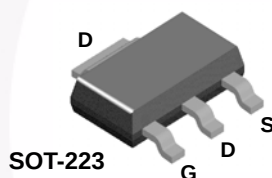
- $R_{DS(on)} = 121\text{ m}\Omega$ (Typ.)@ $V_{GS} = 10\text{ V}$, $I_D = 2.8\text{ A}$
- $R_{DS(on)} = 156\text{ m}\Omega$ (Typ.)@ $V_{GS} = 5\text{ V}$, $I_D = 1.8\text{ A}$
- 低栅极电荷 (典型值 2.9 nC)
- 低 C_{rss} (典型值 2.04 pF)
- 快速开关
- 100% 经过雪崩测试
- 改善的 dv/dt 处理能力
- 符合 RoHS 标准

说明

该 N 沟道 MOSFET 采用飞兆半导体的先进 Power Trench® 工艺生产, 这一先进工艺专用于最小化通态电阻, 同时保持卓越的开关性能。

应用

- 消费电子设备
- LED 电视和显示器
- 同步整流
- 不间断电源
- 微型太阳能逆变器



MOSFET 最大额定值 $T_C = 25\text{ }^\circ\text{C}$ 除非另有说明。

符号	参数	FDT1600N10ALZ	单位
V_{DSS}	漏极-源极电压	100	V
V_{GSS}	栅极-源极电压	± 20	V
I_D	漏极电流	—连续 ($T_C = 25\text{ }^\circ\text{C}$)	A
		—连续 ($T_C = 100\text{ }^\circ\text{C}$)	
I_{DM}	漏极电流	—脉冲 (注 2)	A
E_{AS}	单脉冲雪崩能量	(注 3)	mJ
dv/dt	二极管恢复 dv/dt 峰值	(注 4)	V/ns
P_D	功耗	($T_C = 25\text{ }^\circ\text{C}$)	10.42
		—超过 $25\text{ }^\circ\text{C}$ 时降额	0.083
T_J, T_{STG}	工作和存储结温范围	-55 至 +150	$^\circ\text{C}$
T_L	用于焊接的最大引脚温度, 距离外壳 1/8", 持续 5 秒	300	$^\circ\text{C}$

热性能

$R_{\theta JC}$	结至外壳热阻最大值	(注 1)	12	$^\circ\text{C/W}$
$R_{\theta JA}$	结至环境热阻最大值	(注 1a)	60	

封装标识与订购信息

器件编号	顶标	封装	包装方法	卷尺寸	带宽	数量
FDT1600N10ALZ	16010ALZ	SOT-223	卷带	13"	12 mm	4000 单元

电气特性 $T_J = 25^\circ\text{C}$ 除非另有说明。

符号	参数	测试条件	最小值	典型值	最大值	单位
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关断特性

BV_{DSS}	漏极-源极击穿电压	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$	100	-	-	V
$\Delta BV_{DSS} / DT_J$	击穿电压温度系数	$I_D = 250\ \mu\text{A}$, 参考 25°C	-	0.1	-	V/ $^\circ\text{C}$
I_{DSS}	零栅极电压漏极电流	$V_{DS} = 80\ \text{V}$, $V_{GS} = 0\ \text{V}$	-	-	1	μA
		$V_{DS} = 80\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_C = 125^\circ\text{C}$	-	-	500	
I_{GSS}	栅极-源极漏电流	$V_{GS} = \pm 20\ \text{V}$, $V_{DS} = 0\ \text{V}$	-	-	± 10	μA

导通特性

$V_{GS(th)}$	栅极阈值电压	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	1.4	-	2.8	V
$R_{DS(on)}$	漏极至源极静态导通电阻	$V_{GS} = 10\ \text{V}$, $I_D = 2.8\ \text{A}$	-	121	160	$\text{m}\Omega$
		$V_{GS} = 5\ \text{V}$, $I_D = 1.8\ \text{A}$	-	156	375	$\text{m}\Omega$
g_{FS}	正向跨导	$V_{DS} = 10\ \text{V}$, $I_D = 5.6\ \text{A}$	-	26.1	-	S

动态特性

C _{iss}	输入电容	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		-	169	225	pF
C _{oss}	输出电容			-	43	55	pF
C _{rss}	反向传输电容			-	2.04	-	pF
C _{oss(er)}	能源相关输出电容	V _{DS} = 50 V, V _{GS} = 0 V		-	85	-	pF
Q _{g(tot)}	10V 的栅极电荷总量	V _{GS} = 10 V	V _{DD} = 50 V, I _D = 5.6 A	-	2.9	3.77	nC
Q _{g(tot)}	5V 的栅极电荷总量	V _{GS} = 5 V		-	1.6	2.08	nC
Q _{gs}	栅极—源极栅极电荷			-	0.7	-	nC
Q _{gd}	栅极—漏极“密勒”电荷			-	0.64	-	nC
V _{plateau}	栅极电场电压			(注 5)	-	3.81	-
Q _{sync}	总栅极电荷同步	V _{DS} = 0 V, I _D = 2.8 A		-	2.45	-	nC
Q _{oss}	输出电荷	V _{DS} = 50 V, V _{GS} = 0 V		-	5.2	-	nC
ESR	等效串联电阻 (G-S)	f = 1 MHz		-	2.1	-	Ω

开关特性

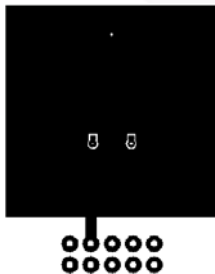
$t_{d(on)}$	导通延迟时间	$V_{DD} = 50\ \text{V}$, $I_D = 5.6\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_G = 4.7\ \Omega$	-	7.4	24.8	ns
t_r	上升时间		-	2.5	15	ns
$t_{d(off)}$	关断延迟时间		-	13.5	37	ns
t_f	关断下降时间	(注 5)	-	2.4	14.8	ns

漏极-源极二极管特性

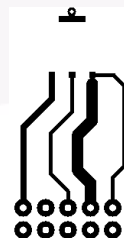
I _S	漏极－源极二极管最大连续正向电流		-	-	5.6	A
I _{SM}	漏极－源极二极管最大正向脉冲电流		-	-	11.2	A
V _{SD}	源极－漏极二极管正向电压	V _{GS} = 0 V, I _{SD} = 5.6 A	-	-	1.3	V
t _{rr}	反向恢复时间	V _{GS} = 0 V, I _{SD} = 5.6 A, V _{DD} = 50V,	-	34.1	-	ns
Q _{rr}	反向恢复电荷	dI _F /dt = 100A/μs	-	32.7	-	nC

注:

1. $R_{\theta JA}$ 等于结至壳体和壳体至环境热阻之和, 其中, 壳体热参考定义为漏极引脚的焊料安装表面。
 $R_{\theta JC}$ 由设计保证, 而 $R_{\theta CA}$ 由用户的板设计确定。



a) 60 安装在 2 oz 的最小 1 in² 铜焊盘上时的 $^\circ\text{C}/\text{W}$ 。



b) 118 安装在 2 oz 的最小铜焊盘上时的 $^\circ\text{C}/\text{W}$ 。

2. 重复额定值: 脉冲宽度受限于最大结温。
 3. 启动 $T_J = 25^\circ\text{C}$, $L = 3\ \text{mH}$, $I_{AS} = 2.47\ \text{A}$ 。
 4. $I_{SD} \leq 5.6\ \text{A}$, $di/dt \leq 200\ \text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, 启动 $T_J = 25^\circ\text{C}$ 。
 5. 本质上独立于工作温度的典型特性。

典型性能特征

图 1. 导通区域特性

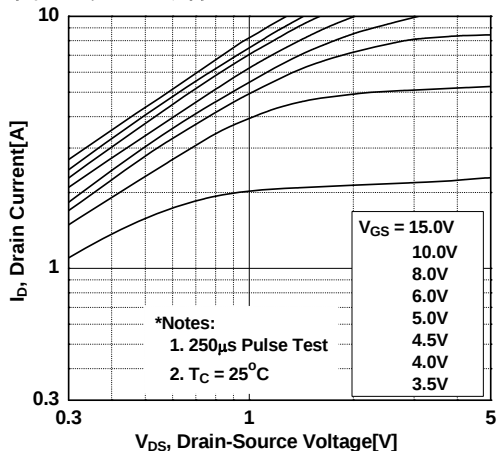


图 2. 传输特性

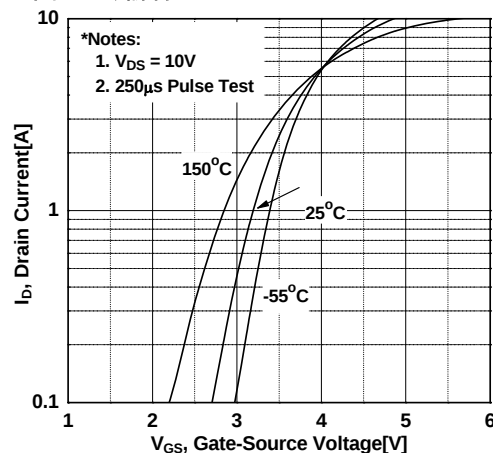


图 3. 导通电阻变化与漏极电流和栅极电压

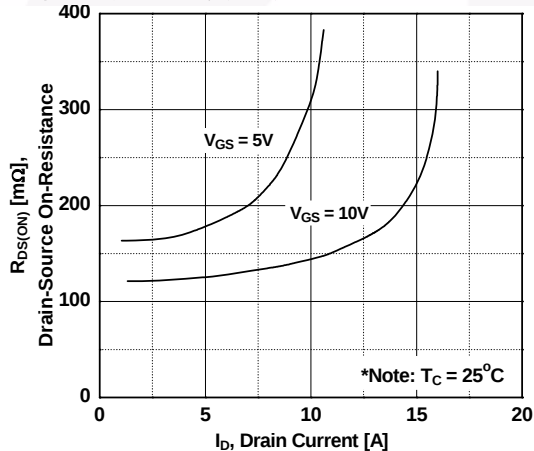


图 4. 体二极管正向电压变化与源电流和温度

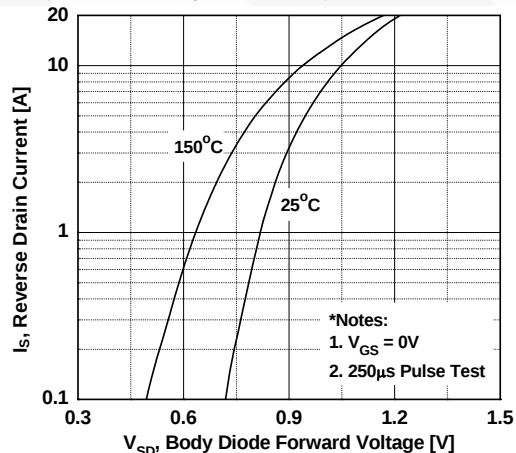


图 5. 电容特性

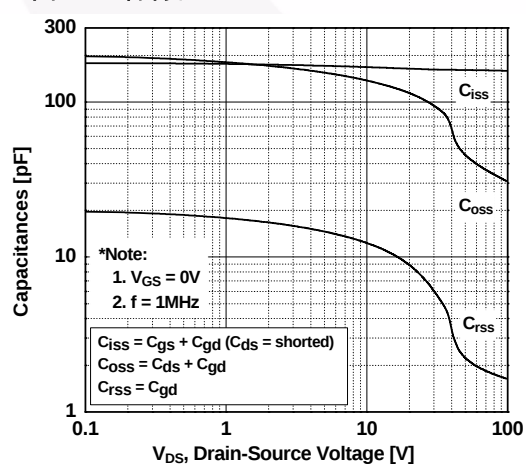
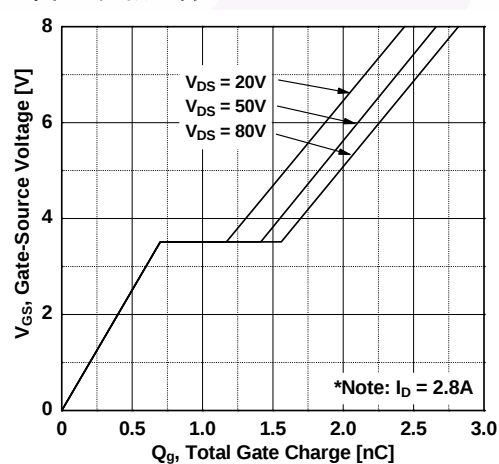


图 6. 栅极电荷



典型性能特征 (接上页)

图 7. 击穿电压变化与温度

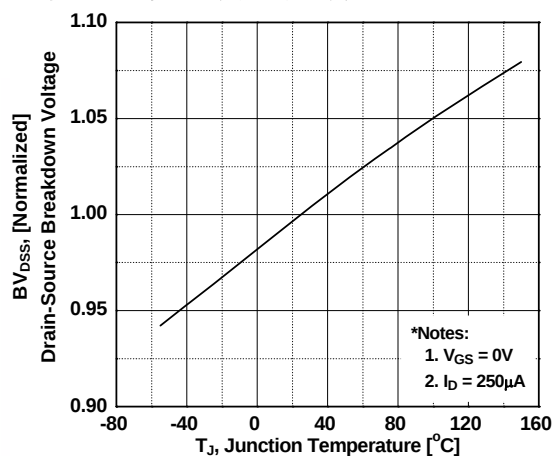


图 8. 导通电阻变化与温度

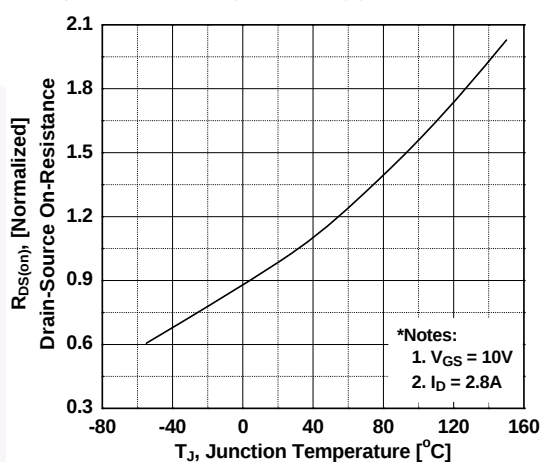


图 9. 最大安全工作区

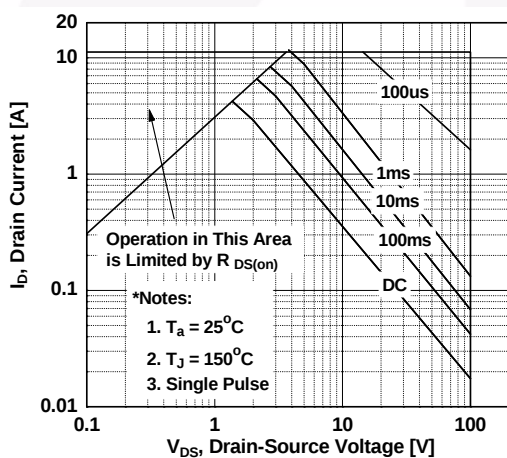


图 10. 最大漏极电流与壳体温度

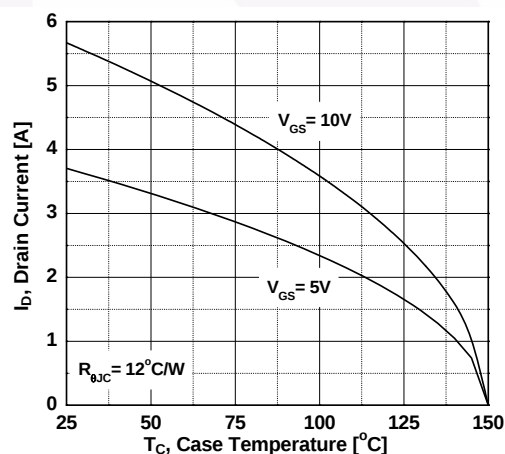


图 11. E_oss 与漏极至源极电压

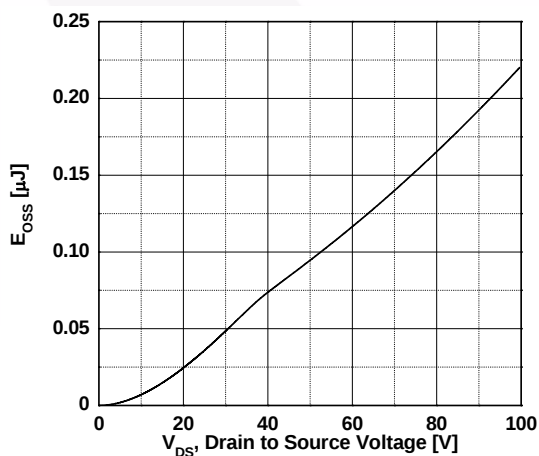
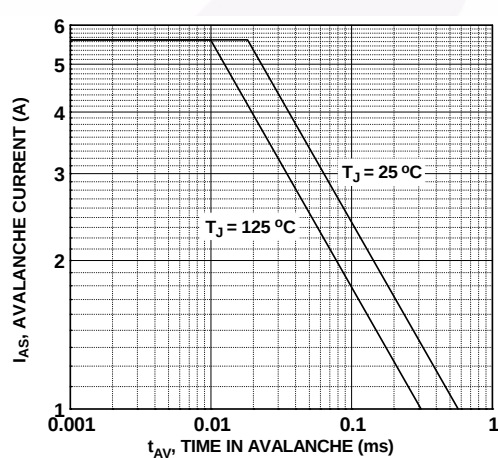
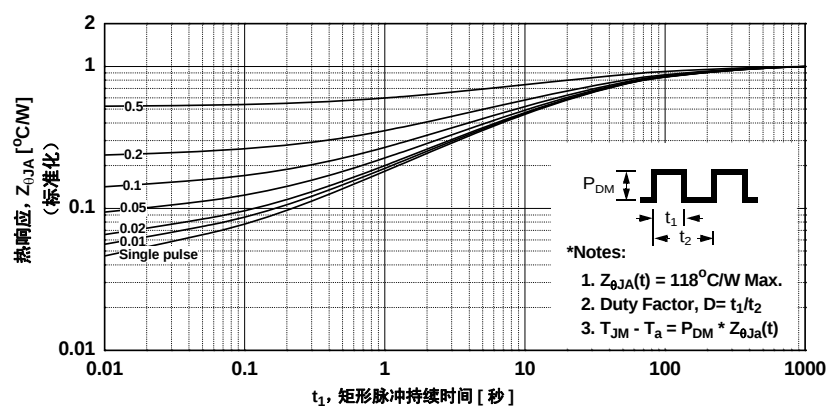


图 12. 非箝位感性开关能力



典型性能特征 (接上页)

图 13. 瞬态热响应曲线



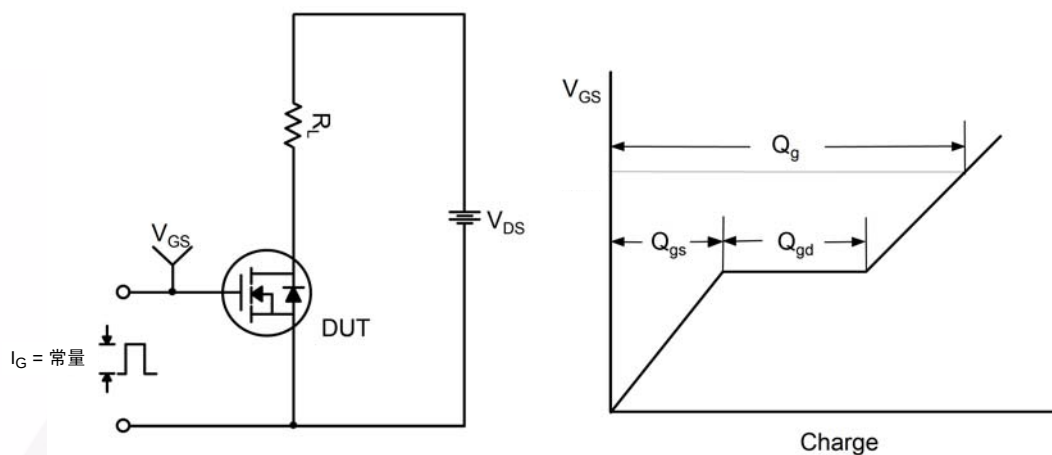


图 14. 栅极电荷测试电路与波形

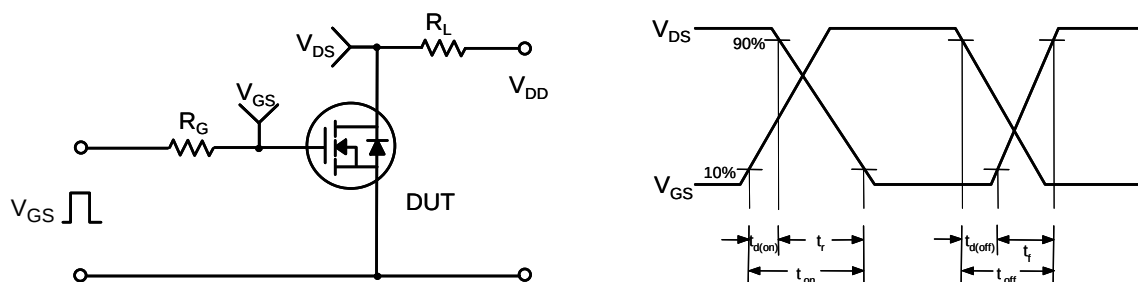


图 15. 阻性开关测试电路与波形

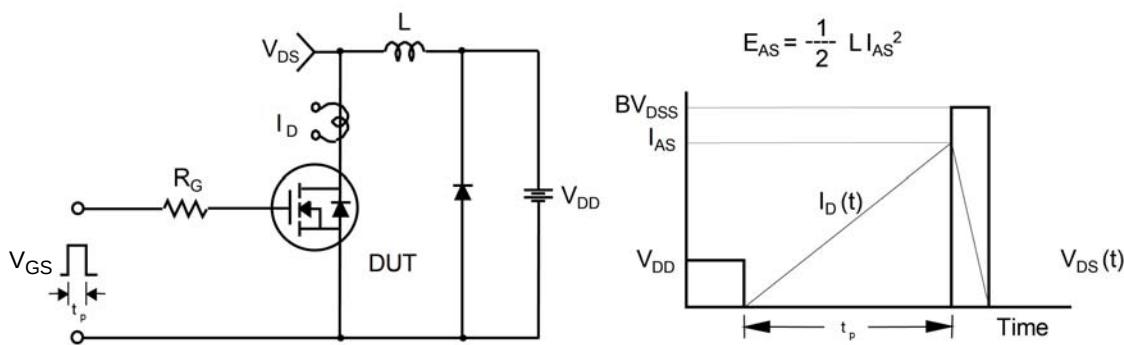


图 16. 非箝位感性开关测试电路与波形

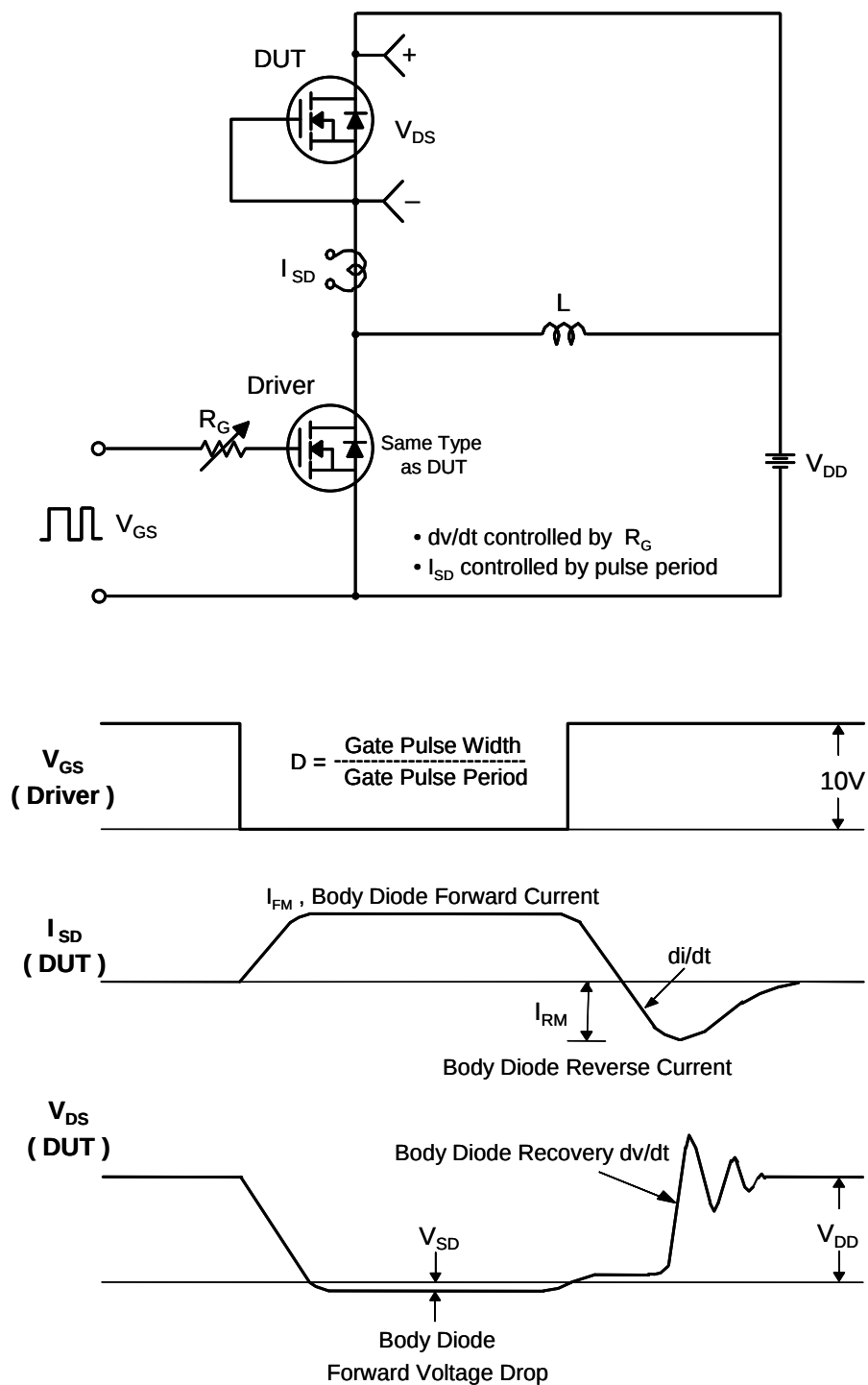


图 17. 二极管恢复 dv/dt 峰值测试电路与波形

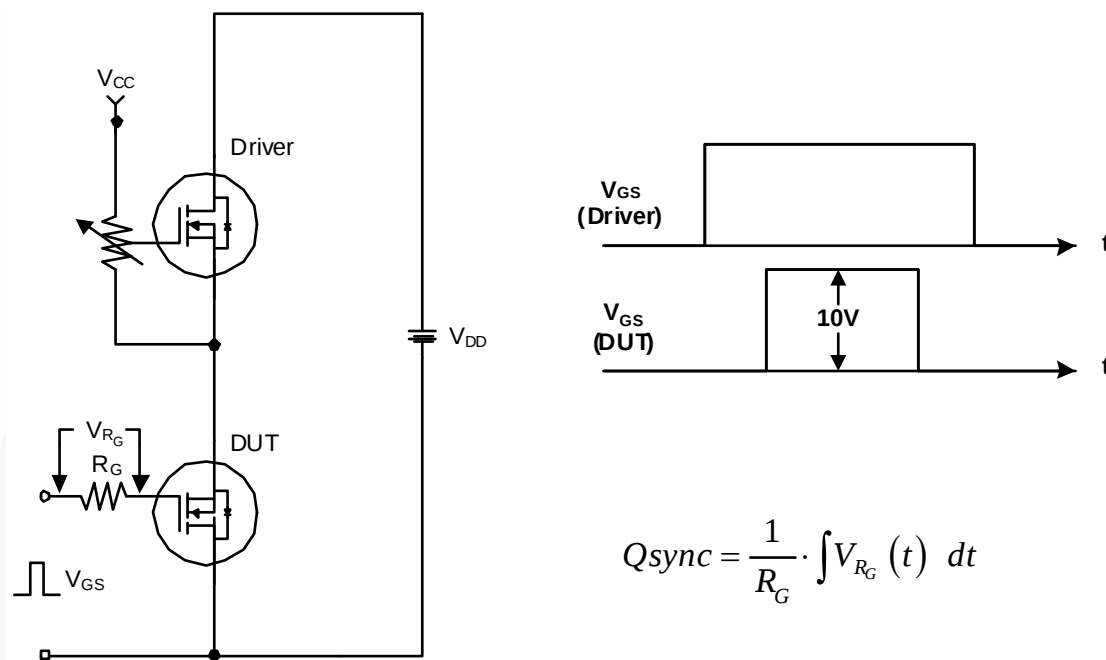


图 18. 总栅极电荷 Q_{sync} . 测试电路和波形

机械尺寸

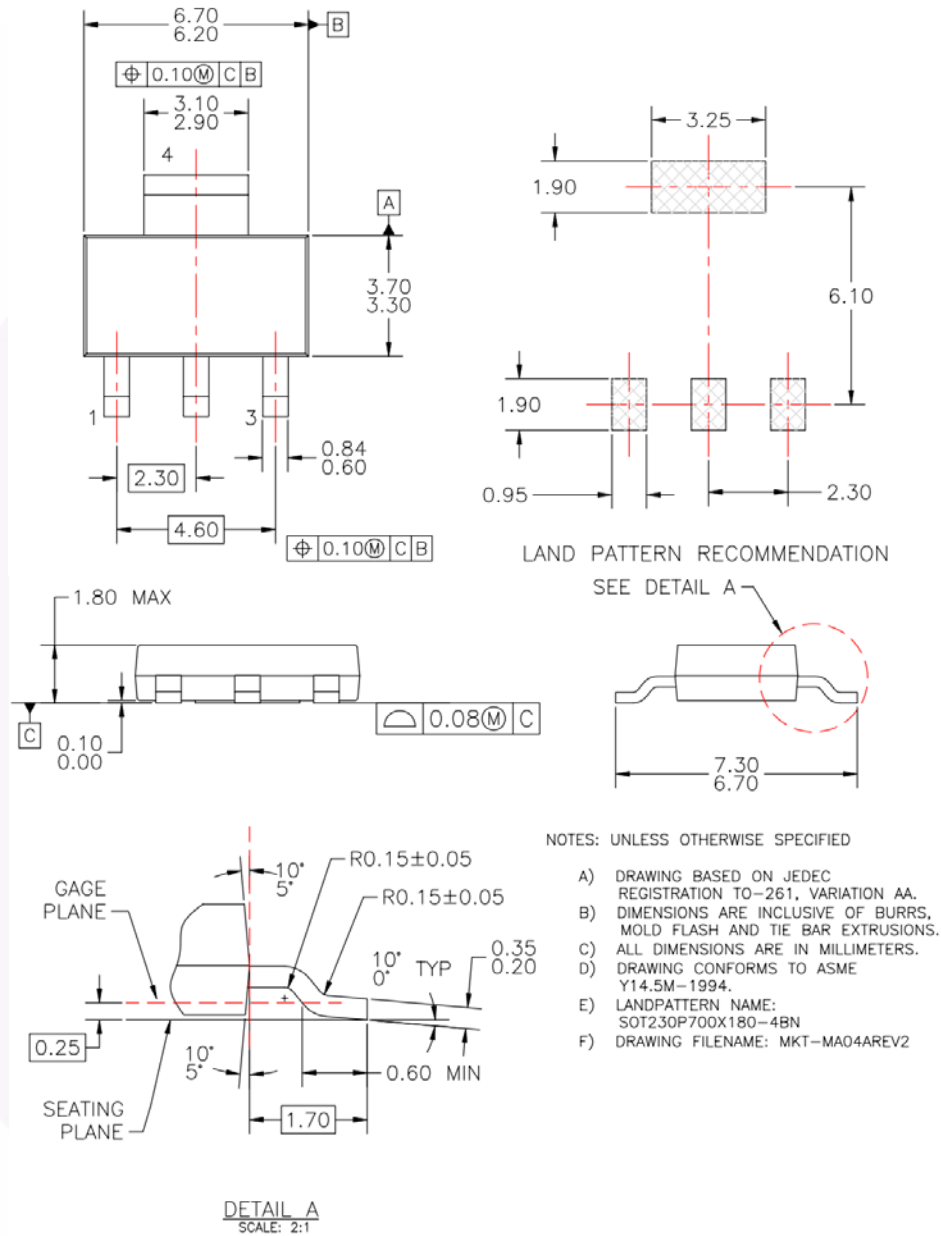


图 19. SOT-223, 模塑, 4 引脚

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